

FQH90N15 / FQA90N15

N-Channel Power MOSFET

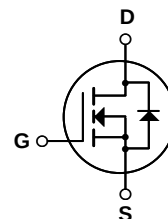
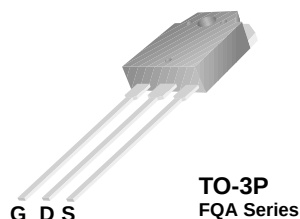
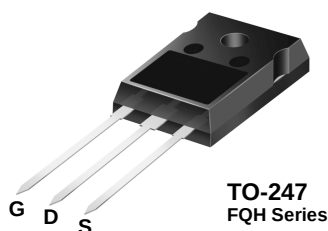
Features

- 90A, 150V, $R_{DS(on)} = 0.018\Omega$ @ $V_{GS} = 10\text{ V}$
- Low gate charge (typical 220 nC)
- Low C_{RSS} (typical 200 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifiers, high efficiency switching for DC/DC converters, and DC motor control, uninterrupted power supply.



Absolute Maximum Ratings

Symbol	Parameter	FQH90N15/FQA90N15	Unit
V_{DSS}	Drain-Source Voltage	150	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	90 63.5	A A
I_{DM}	Drain Current - Pulsed (Note 1)	360	A
V_{GSS}	Gate-Source voltage	± 25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	1400	mJ
I_{AR}	Avalanche Current (Note 1)	90	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	37.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	375 2.5	W W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Min.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.4	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	150	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	--	0.15	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 150V, V _{GS} = 0V V _{DS} = 120V, T _C = 150°C	-- --	-- --	1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25V, V _{DS} = 0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25V, V _{DS} = 0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 45A	--	0.014	0.018	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 45A (Note 4)	--	68	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	--	6700	8700	pF
C _{oss}	Output Capacitance		--	1400	1800	pF
C _{rss}	Reverse Transfer Capacitance		--	200	260	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 75V, I _D = 90A R _G = 25Ω (Note 4, 5)	--	105	220	ns
t _r	Turn-On Rise Time		--	760	1500	ns
t _{d(off)}	Turn-Off Delay Time		--	470	950	ns
t _f	Turn-Off Fall Time		--	410	830	ns
Q _g	Total Gate Charge	V _{DS} = 120V, I _D = 90A V _{GS} = 10V (Note 4, 5)	--	220	285	nC
Q _{gs}	Gate-Source Charge		--	43	--	nC
Q _{gd}	Gate-Drain Charge		--	110	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	90	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	360	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 90A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 90A dI _F /dt =100A/μs (Note 4)	--	175	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.97	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 0.29\text{mH}$, $I_{AS} = 90A$, $V_{DD} = 25V$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 90A$, $dI/dt \leq 300A/\mu s$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

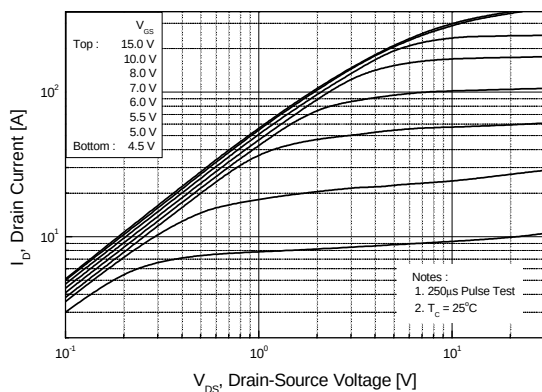


Figure 2. Transfer Characteristics

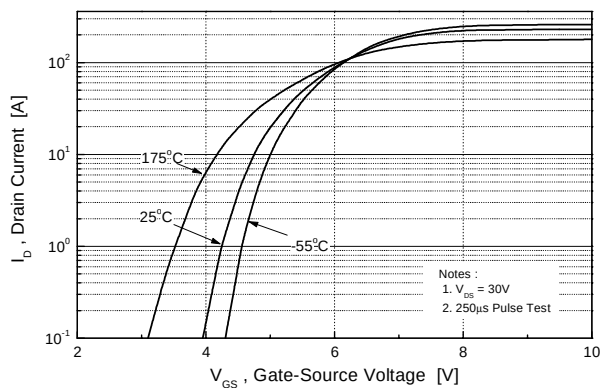


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

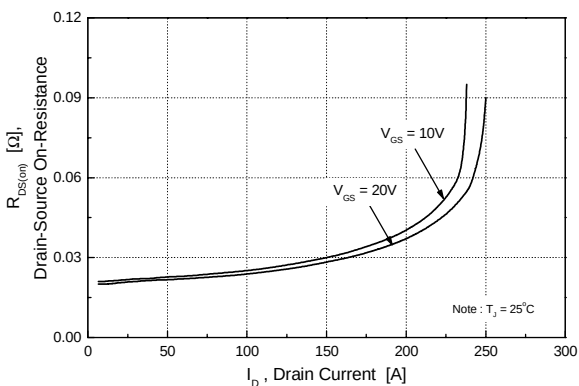


Figure 4. Body Diode Forward Voltage Variation vs. Source Current

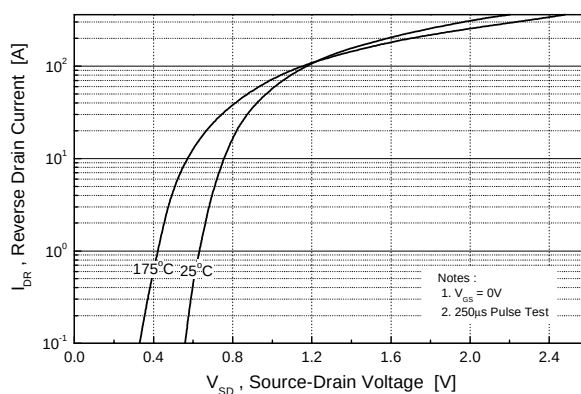


Figure 5. Capacitance Characteristics

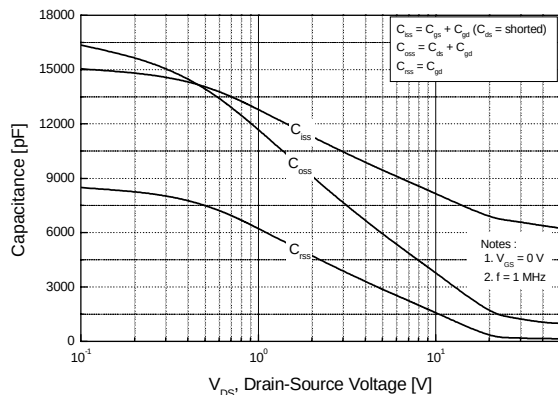
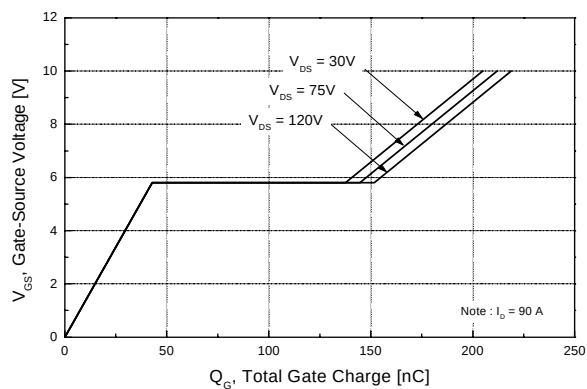


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

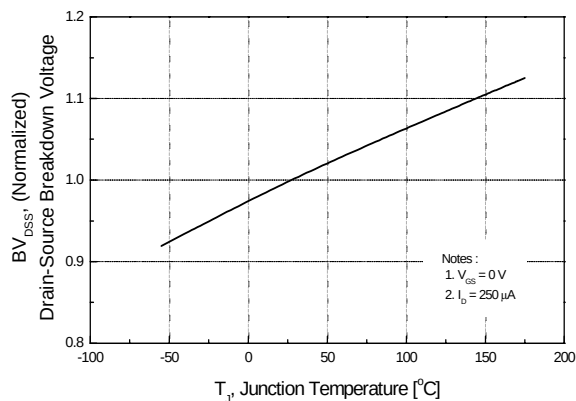


Figure 8. On-Resistance Variation vs. Temperature

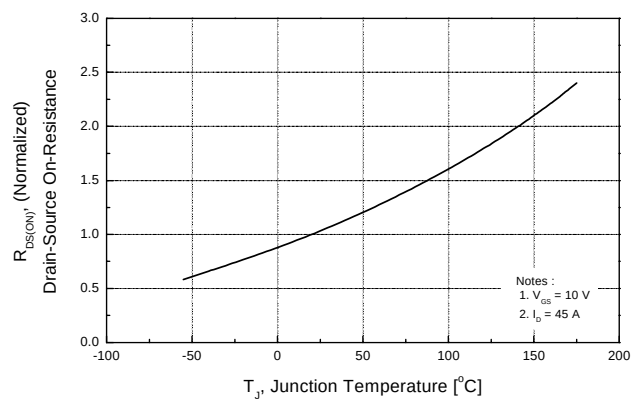


Figure 9. Maximum Safe Operating Area

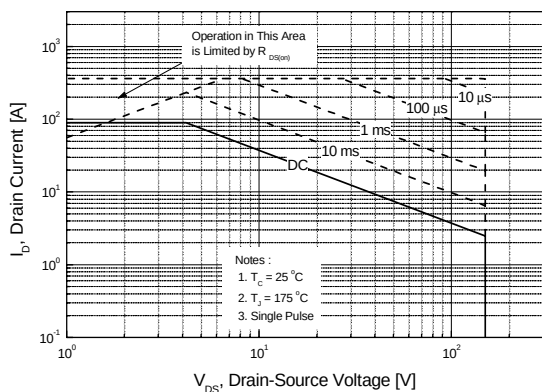


Figure 10. Maximum Drain Current vs. Case Temperature

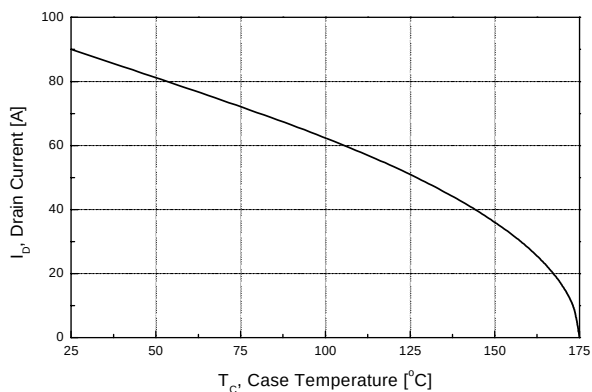
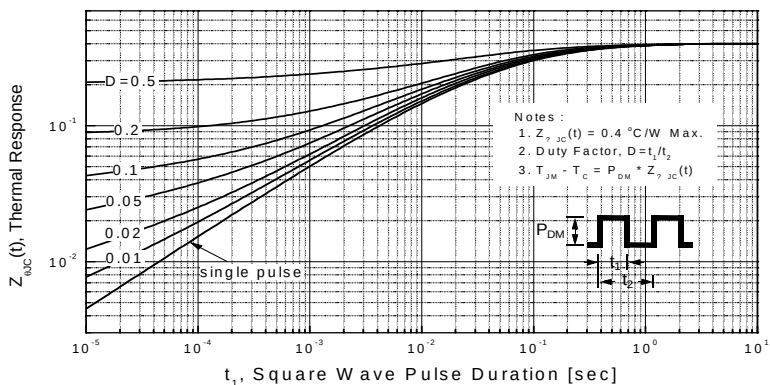
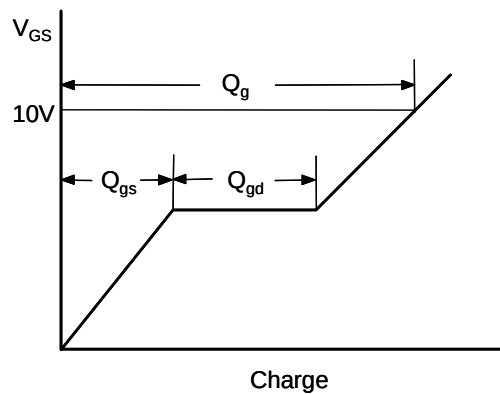
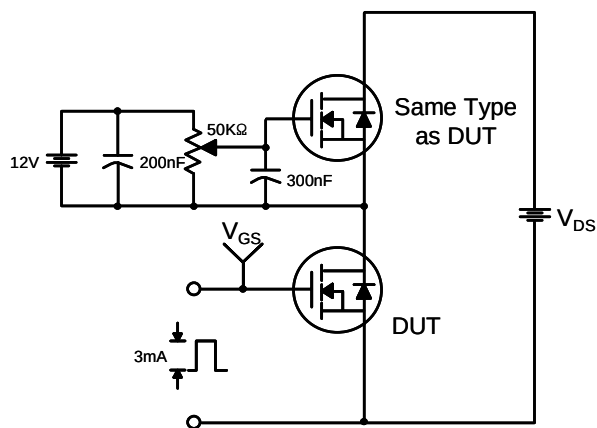


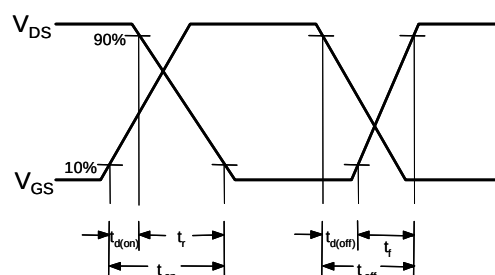
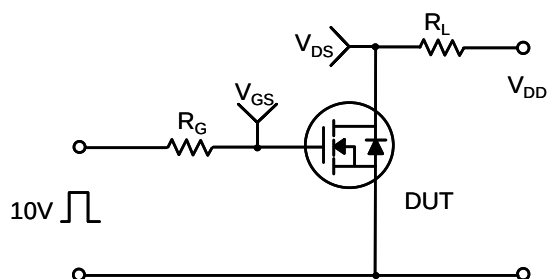
Figure 11. Transient Thermal Response Curve



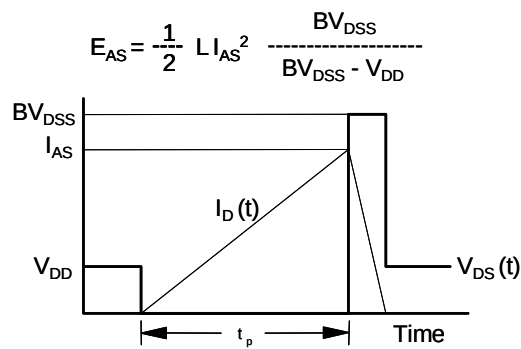
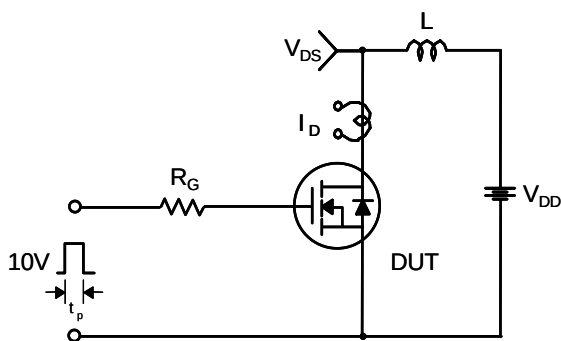
Gate Charge Test Circuit & Waveform



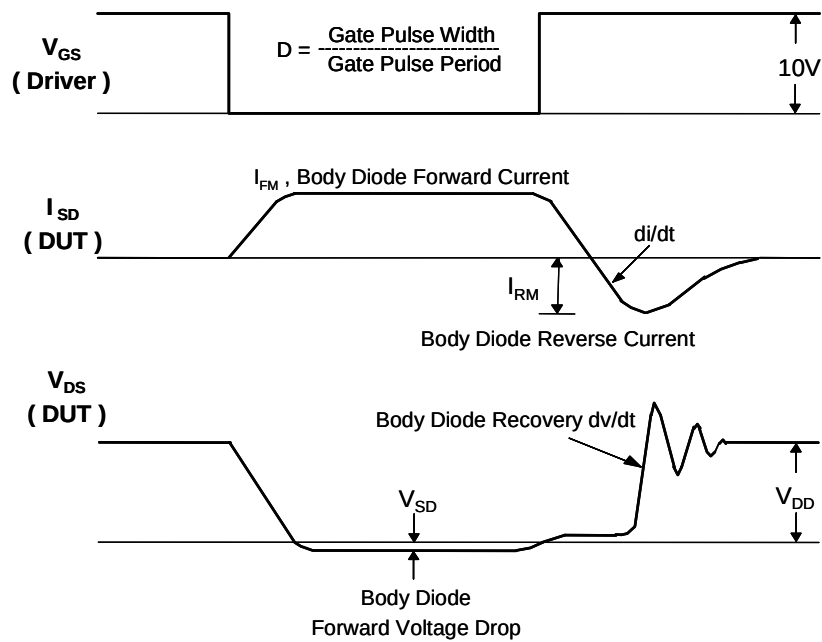
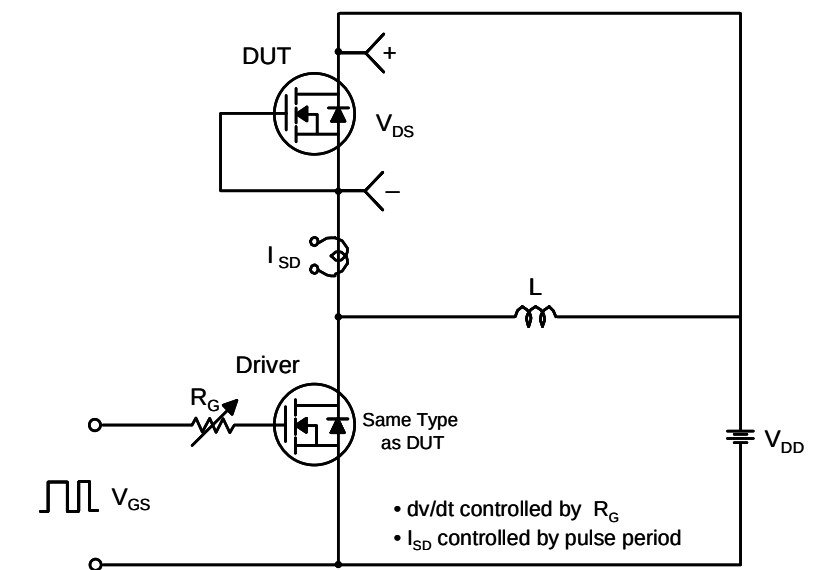
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



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